

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	9.5mΩ @ V _{GS} = 10V	55A
	11.5mΩ @ V _{GS} = 4.5V	50A

Description

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

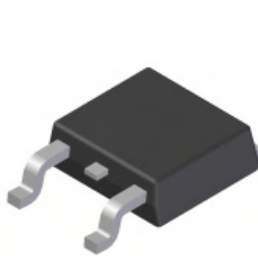
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

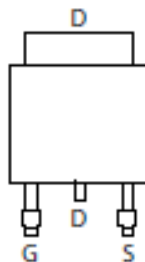
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) test in production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

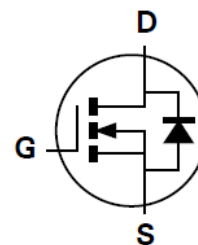
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



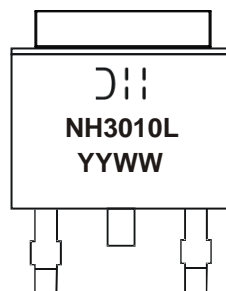
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH3010LK3-13	TO252 (DPAK)	2500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



⌋⌋⌋ = Manufacturer's Marking
 NH3010L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 15 = 2015)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _C = +25°C T _C = +100°C	I _D	55 40	A
	Steady State	T _A = +25°C T _A = +100°C	I _D	15 10.6	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	100	A
Avalanche Current (Note 7) L = 0.8mH			I _{AS}	15	A
Avalanche Energy (Note 7) L = 0.8mH			E _{AS}	75	mJ

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	74	°C/W
	t < 10s			31	°C/W
Total Power Dissipation (Note 6)			P _D	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	47	°C/W
	t < 10s			21	°C/W
Thermal Resistance, Junction to Case (Note 6)			R _{θJC}	2.5	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8	9.5	mΩ	V _{GS} = 10V, I _D = 18A
		—	10	11.5		V _{GS} = 4.5V, I _D = 16A
Diode Forward Voltage	V _{SD}	—	0.75	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2075	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	190	—		
Reverse Transfer Capacitance	C _{rss}	—	138	—		
Gate Resistance	R _g	—	2.4	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	16.1	—	nC	V _{DS} = 15V, I _D = 18A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	37	—		
Gate-Source Charge	Q _{gs}	—	6.1	—		
Gate-Drain Charge	Q _{gd}	—	5.9	—		
Turn-On Delay Time	t _{D(ON)}	—	4.5	—	ns	V _{DS} = 15V, V _{GS} = 10V, R _L = 0.83Ω, R _{GEN} = 3Ω
Turn-On Rise Time	t _R	—	19.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	31	—		
Turn-Off Fall Time	t _F	—	10.7	—		
Reverse Recovery Time	t _{RR}	—	13.7	—	ns	I _F = 15A, di/dt = 500A/μs
Reverse Recovery Charge	Q _{RR}	—	18.3	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

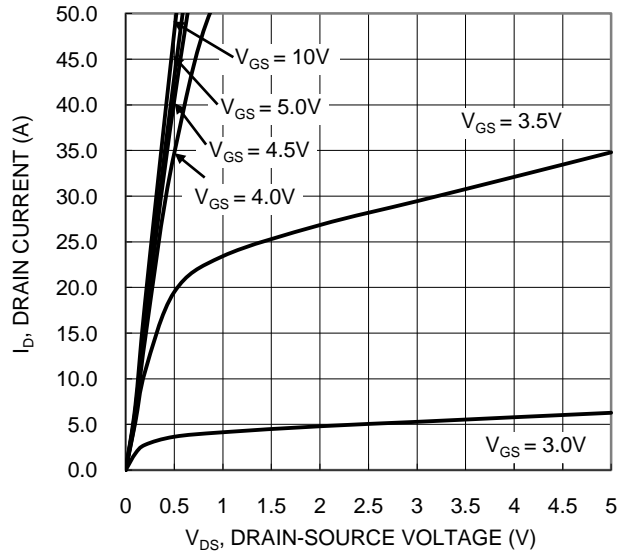


Figure 1. Typical Output Characteristic

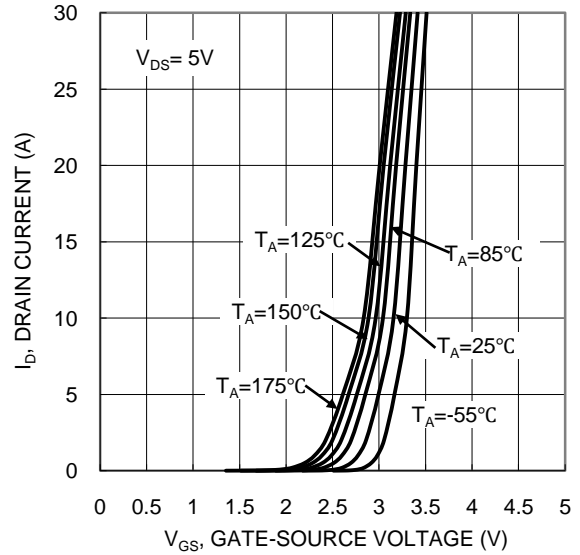


Figure 2. Typical Transfer Characteristic

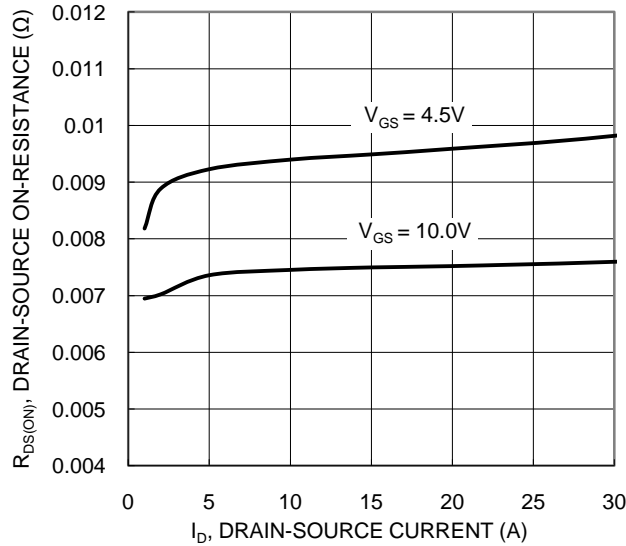


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

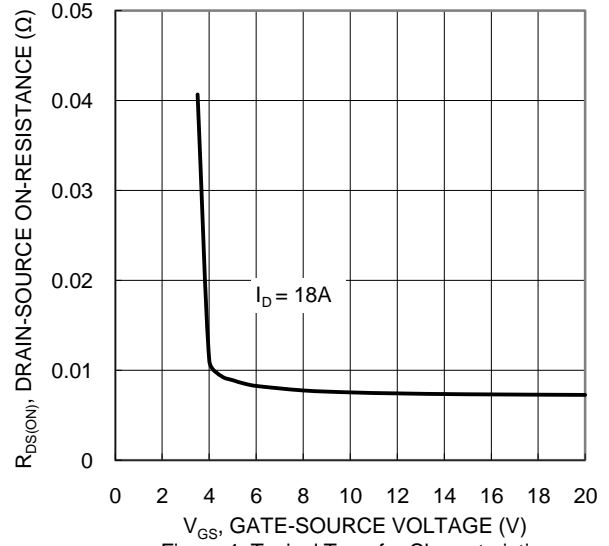


Figure 4. Typical Transfer Characteristic

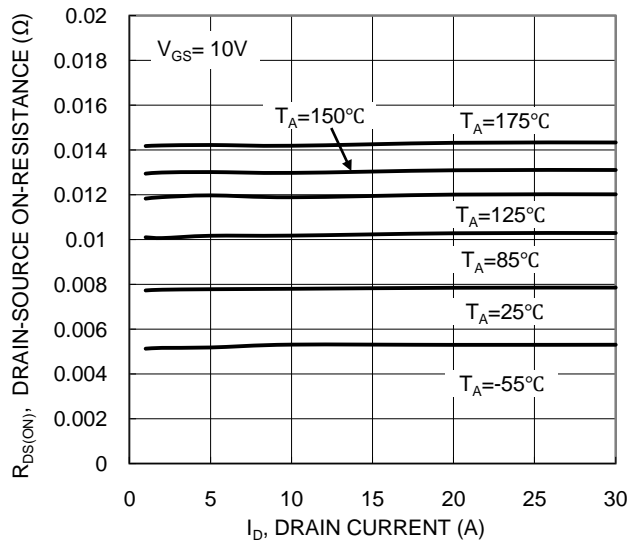


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

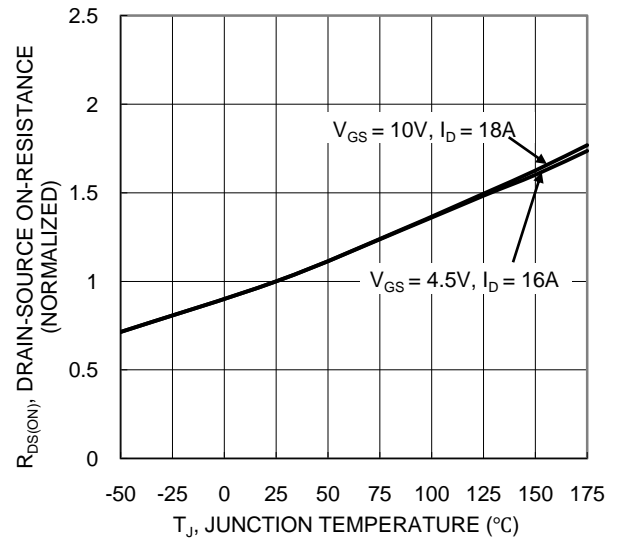


Figure 6. On-Resistance Variation with Temperature

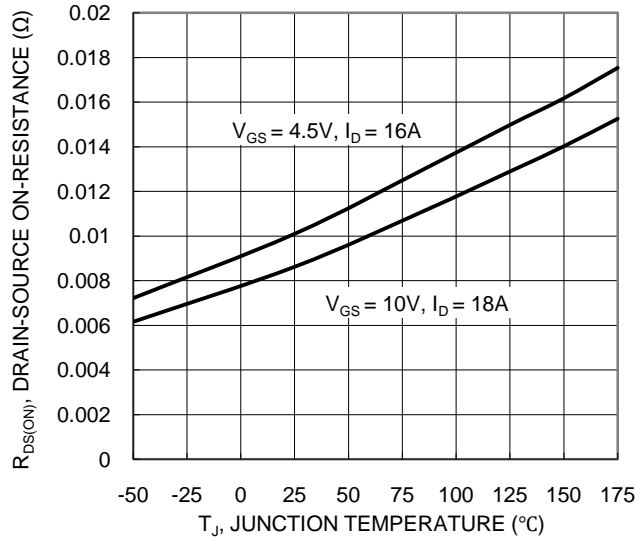


Figure 7. On-Resistance Variation with Temperature

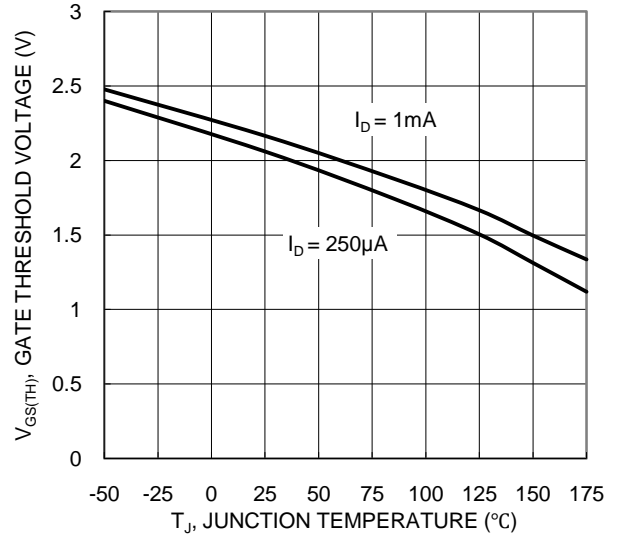


Figure 8. Gate Threshold Variation vs. Junction Temperature

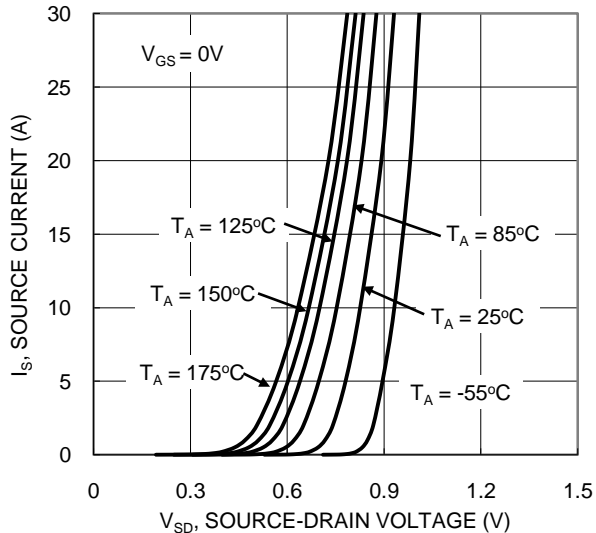


Figure 9. Diode Forward Voltage vs. Current

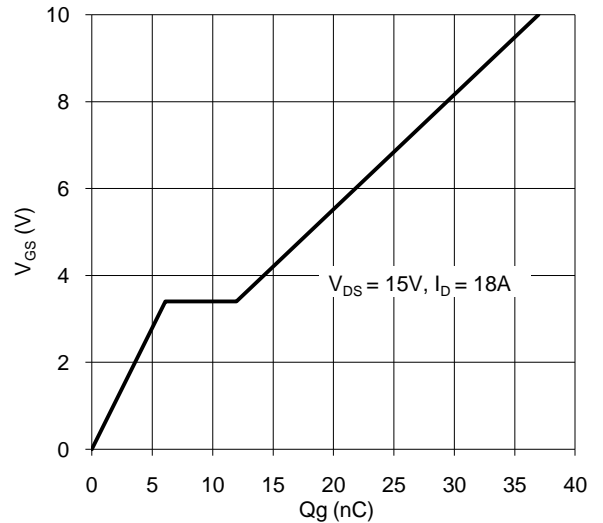


Figure 10. Gate Charge

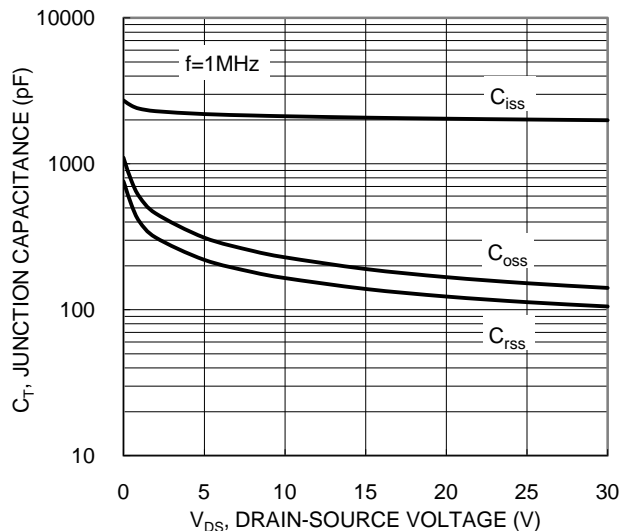


Figure 11. Typical Junction Capacitance

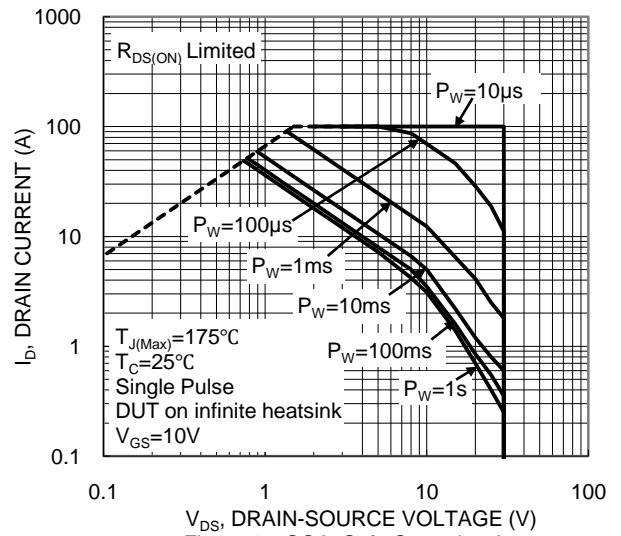


Figure 12. SOA, Safe Operation Area

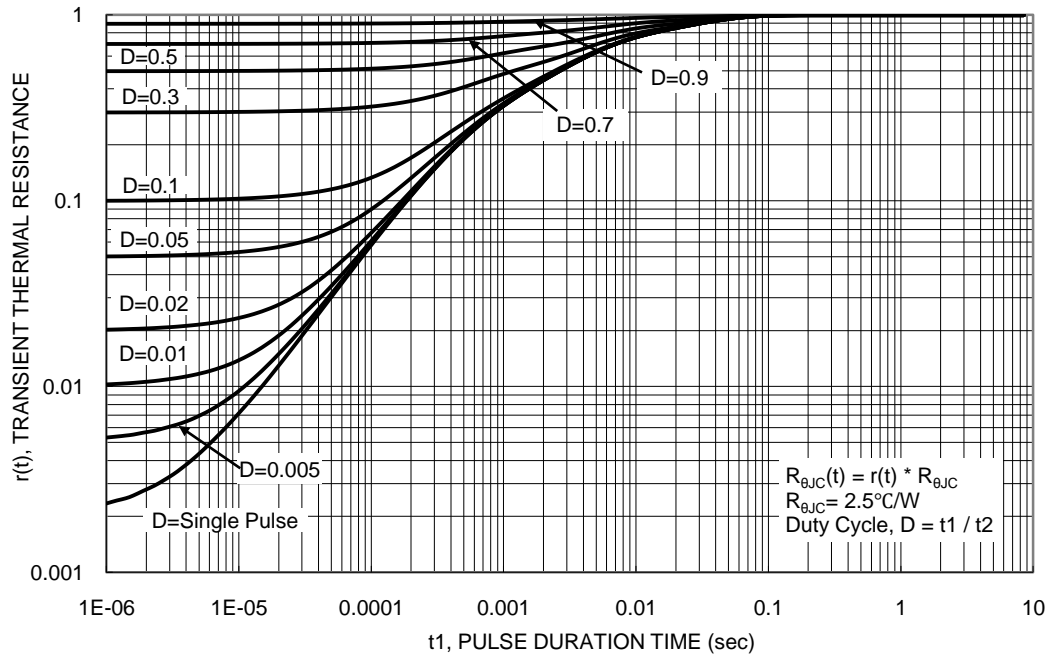
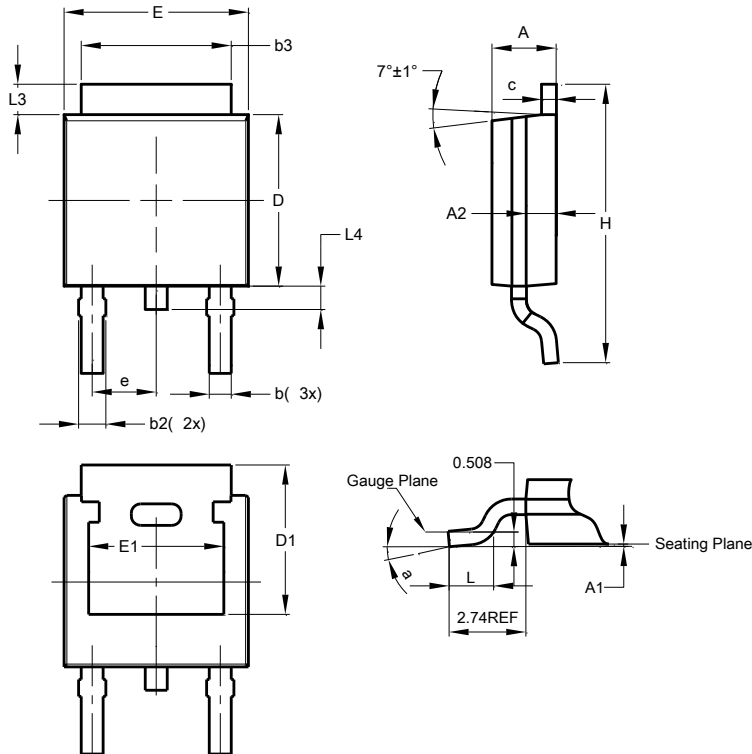


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)

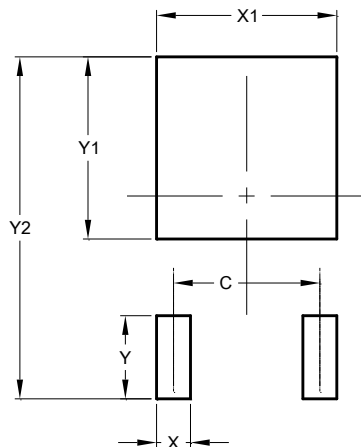


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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